

Accepted Manuscript

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PII: S0040-6090(17)30455-8
DOI: doi: [10.1016/j.tsf.2017.06.020](https://doi.org/10.1016/j.tsf.2017.06.020)
Reference: TSF 36027
To appear in: *Thin Solid Films*
Received date: 8 October 2016
Revised date: 5 June 2017
Accepted date: 8 June 2017

Please cite this article as: Jing Li, Zhenghong Wei, Tongqing Wang, Jie Cheng, Qingqiang He , A theoretical model incorporating both the nano-scale material removal and wafer global uniformity during planarization process, *Thin Solid Films* (2017), doi: [10.1016/j.tsf.2017.06.020](https://doi.org/10.1016/j.tsf.2017.06.020)

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A theoretical model incorporating both the nano-scale material removal and wafer global uniformity during planarization process

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Abstract

In the ultra large-scale integration process, as chemical mechanical polishing (CMP) is developing to higher precision, nano level planarity and sub-nano level roughness of wafer surfaces become key problems to be overcome. In this work, a theoretical model for local and total material removal was proposed based on the particle sliding trajectories and chemical-mechanical synergy, and the material removal distribution on wafer surface were analyzed. Furthermore, the chemical-mechanical mechanism was studied and synergy maps constructed. It is found that the passivation-wear and additive-synergistic effects dominate the material removal during CMP. This study establishes a correlation mechanism between the nano material removal and global uniformity of wafer surfaces, which provides theoretical and experimental framework for optimizing the slurry and the process parameters.

Keywords: Chemical mechanical polishing; Wear modelling; Corrosion-wear;

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